

SILICON POWER TRANSISTOR 2SA1650

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1650 is a mold power transistor developed for highspeed switching and features a very low collector-to-emitter saturation. This transistor is ideal for use in switching power supplies, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for high-current switching.

FEATURES

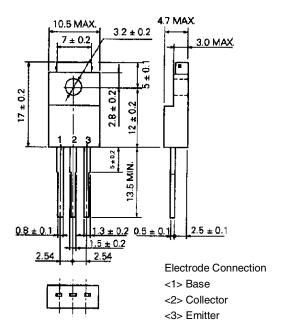
- Mold package that does not require an insulating board or insulation bushing
- · Fast switching speed
- Low collector-to-emitter saturation voltage: $V_{CE(sat)} \le -0.3 \text{ V (MAX.)} @Ic = -3 \text{ A}$

QUALITY GRADES

Standard

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

PACKAGE DRAWING (UNIT: mm)



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------------------|-------------------------------|-------------|------|
| Collector to base voltage | Vсво | | -150 | ٧ |
| Collector to emitter voltage | VCEO | | -100 | V |
| Emitter to base voltage | VEBO | | -7.0 | V |
| Collector current | I _{D(DC)} | | -5.0 | Α |
| Collector current | IC(pulse) | PW ≤ 300 µs, duty cycle ≤ 10% | -10 | Α |
| Base current | I _{B(DC)} | | -2.5 | Α |
| Total power dissipation | Рт | Tc = 25°C | 25 | W |
| Total power dissipation | Рт | Ta = 25°C | 2.0 | W |
| Junction temperature | Tj | | 150 | °C |
| Storage temperature | Tstg | | -55 to +150 | °C |

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

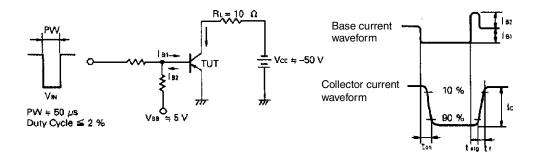
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|------------------------------|-------------------------|---|------|------|------|------|
| Collector cutoff current | Ісво | $V_{CB} = -100 \text{ V}, I_E = 0$ | | | -10 | μΑ |
| Emitter cutoff current | ІЕВО | V _{EB} = -5 V, Ic = 0 | | | -10 | μΑ |
| DC current gain | h _{FE1} * | $V_{CE} = -2 \text{ V, Ic} = -0.5 \text{ A}$ | 100 | | | - |
| DC current gain | hFE2* | $V_{CE} = -2 \text{ V, Ic} = -1 \text{ A}$ | 100 | | 400 | _ |
| DC current gain | h _{FE3} * | $V_{CE} = -2 \text{ V, Ic} = -3 \text{ A}$ | 60 | | | - |
| Collector saturation voltage | V _{CE(sat)1} * | $I_C = -3 A$, $I_B = -0.15 A$ | | | -0.3 | V |
| Collector saturation voltage | VCE(sat)2* | $I_C = -4 A$, $I_B = -0.2 A$ | | | -0.5 | V |
| Base saturation voltage | V _{BE(sat)1} * | $I_C = -3 A$, $I_B = -0.15 A$ | | | -1.2 | V |
| Base saturation voltage | V _{BE(sat)2} * | $I_C = -4 A$, $I_B = -0.2 A$ | | | -1.5 | V |
| Gain bandwidth product | f⊤ | $V_{CE} = -10 \text{ V}, \text{ Ic} = -0.5 \text{ A}$ | | 150 | | MHz |
| Collector capacitance | Cob | $V_{CB} = -10 \text{ V}, \text{ I}_E = 0, \text{ f} = 1 \text{ MHz}$ | | 130 | | pF |
| Turn-on time | ton | Ic = -3 A, I _{B1} = $-I_{B2}$ = -0.15 A, R _L = 10 Ω , Vcc = -50 V Refer to the test circuit. | | 0.3 | | μs |
| Storage time | tstg | | | 1.5 | | μs |
| Fall time | t f | Tiord to the test enount. | | 0.4 | | μs |

^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

hfe CLASSIFICATION

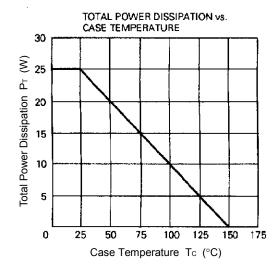
| I | Marking | М | L | K |
|---|------------------|------------|------------|------------|
| I | h _{FE2} | 100 to 200 | 150 to 300 | 200 to 400 |

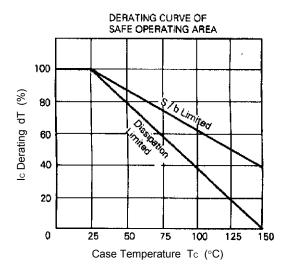
SWITCHING TIME TEST CIRCUIT

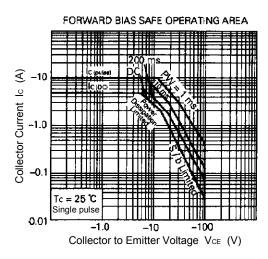


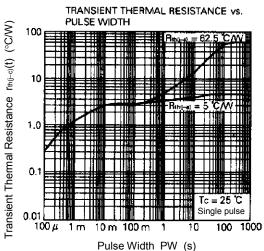


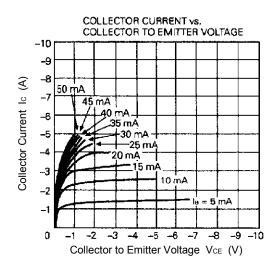
TYPICAL CHARACTERISTICS (Ta = 25°C)

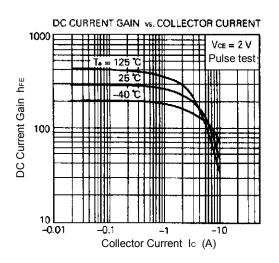




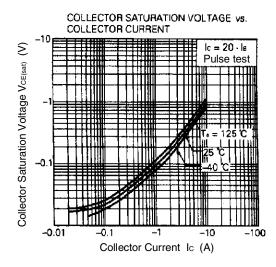


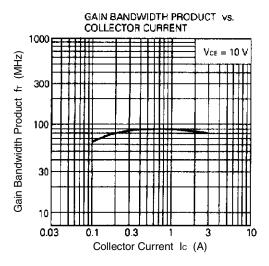


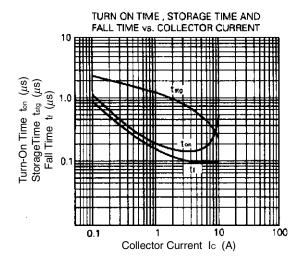


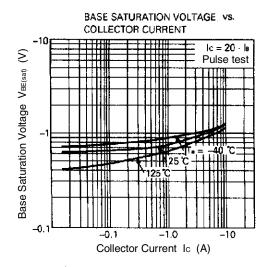


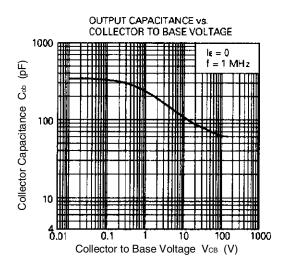
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[MEMO]

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